Yixin

Advanced Power MOSFET SSP5N90A

FEATURES

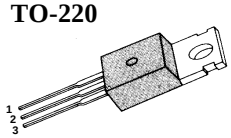
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 25 μA (Max.) @ V_{DS} = 900V
- Low $R_{DS(ON)}$: 2.300 Ω (Typ.)

BV_{DSS} = 900 V

$R_{DS(on)}$ = 2.9 Ω

I_D = 5 A

TO-220



1.Gate 2. Drain 3. Source

Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	900	V
I_D	Continuous Drain Current (T_C=25 °C)	5	A
	Continuous Drain Current (T_C=100 °C)	3.2	
I_{DM}	Drain Current-Pulsed ①	20	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy ②	529	mJ
I_{AR}	Avalanche Current ①	5	A
E_{AR}	Repetitive Avalanche Energy ①	14	mJ
dv/dt	Peak Diode Recovery dv/dt ③	1.5	V/ns
P_D	Total Power Dissipation (T_C=25 °C) Linear Derating Factor	140 1.12	W W/ °C
T_J , T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +150	°C
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8 " from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	0.89	°C /W
$R_{\theta CS}$	Case-to-Sink	0.5	--	
$R_{\theta JA}$	Junction-to-Ambient	--	62.5	

Electrical Characteristics (T_C=25 ℃ unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV_{DSS}	Drain-Source Breakdown Voltage	900	--	--	V	V_{GS}=0V,I_D=250μA
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	1.14	--	V/ ℃	I_D=250μA ***See Fig 7***
$V_{GS(th)}$	Gate Threshold Voltage	2.0	--	3.5	V	V_{DS}=5V,I_D=250μA
I_{GSS}	Gate-Source Leakage , Forward	--	--	100	nA	V_{GS}=30V
	Gate-Source Leakage , Reverse	--	--	-100		V_{GS}=-30V
I_{DSS}	Drain-to-Source Leakage Current	--	--	25	μA	V_{DS}=900V
		--	--	250		V_{DS}=720V,T_C=125 ℃
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	2.9	Ω	V_{GS}=10V,I_D=2.5A ④*
g_{fs}	Forward Transconductance	--	4.0	--	Ω	V_{DS}=50V,I_D=2.5A ④
C_{iss}	Input Capacitance	--	1110	1440	pF	V_{GS}=0V,V_{DS}=25V,f =1MHz ***See Fig 5***
C_{oss}	Output Capacitance	--	105	125		
C_{rss}	Reverse Transfer Capacitance	--	43	50		
$t_{d(on)}$	Turn-On Delay Time	--	21	50	ns	V_{DD}=450V,I_D=5A, R_G=13.6 Ω ***See Fig 13*** ④ ⑤
t_r	Rise Time	--	39	90		
$t_{d(off)}$	Turn-Off Delay Time	--	94	200		
t_f	Fall Time	--	32	75		
Q_g	Total Gate Charge	--	54	70	nC	V_{DS}=720V,V_{GS}=10V, I_D=5A ***See Fig 6 & Fig 12*** ④ ⑤
Q_{gs}	Gate-Source Charge	--	9.0	--		
Q_{gd}	Gate-Drain("Miller") Charge	--	25.0	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I_S	Continuous Source Current	--	--	5	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current ①	--	--	20		
V_{SD}	Diode Forward Voltage ④	--	--	1.4	V	T_J=25℃ ,I_S=5A,V_{GS}=0V
t_{rr}	Reverse Recovery Time	--	540	--	ns	T_J=25℃ ,I_F=5A di_F/dt=100A/μs ④
Q_{rr}	Reverse Recovery Charge	--	5.62	--	μC	

Notes ;

① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
② L=40mH, I_{AS}=5A, V_{DD}=50V, R_G=27Ω, Starting T_J=25 ℃
③ I_{SD} ≤5A, di/dt ≤120A/ μs, V_{DD} ≤ BV_{DSS} , Starting T_J=25 ℃
④ Pulse Test : Pulse Width = 250 μs, Duty Cycle ≤2%
⑤ Essentially Independent of Operating Temperature